

In the claims:

Please amend the claims as follows:

1. (Currently Amended) A method of manufacturing a circuit device comprising the steps of:

preparing a conductive foil and forming an isolation trench having a smaller thickness than that of the conductive foil on the conductive foil in a region excluding where a conductive pattern of a first layer is to be formed, thereby forming the conductive pattern of the first layer;

forming an interlayer insulating film over the conductive pattern of the first layer;

forming plural layers of a conductive pattern on the conductive pattern of the first layer through ~~an~~the interlayer insulating film;

~~mounting~~incorporating a circuit element ~~into~~ onto the conductive pattern ~~which is~~  
~~desirable~~;

covering the circuit element and entirely molding with an insulating resin; and

removing the conductive foil in a ~~thick~~ portion where the isolation trench is not provided.

2. (Original) A method of manufacturing a circuit device according to claim 1 further comprising the step of:

separating the insulating resin through dicing for each circuit device including the circuit element.

3. (Original) The method of manufacturing a circuit device according to claim 1, wherein the conductive foil is constituted by any of copper, aluminum and iron-nickel.

4. (Original) The method of manufacturing a circuit device according to claim 1, wherein the isolation trench to be selectively formed on the conductive foil is provided through chemical or physical etching.

5. (Original) The method of manufacturing a circuit device according to claim 1, wherein a thermosetting resin is used for the interlayer insulating film.

6. (Original) The method of manufacturing a circuit device according to claim 5, wherein a via hole is formed on the interlayer insulating film through a laser.

7. (Original) The method of manufacturing a circuit device according to claim 1, wherein a photosensitive resist layer is used for the interlayer insulating film.

8. (Original) The method of manufacturing a circuit device according to claim 7, wherein a via hole is formed on the interlayer insulating film through photosensitization.

9. (Original) The method of manufacturing a circuit device according to claim 1, wherein the conductive pattern of the layers is formed by a copper plated layer.

10. (Original) The method of manufacturing a circuit device according to claim 9, wherein the copper plated layer is formed by electroless plating and electroplating.

11. (Original) The method of manufacturing a circuit device according to claim 1, wherein the circuit element has either or both of a semiconductor bare chip and a chip circuit component fixed thereto.

12. (Original) The method of manufacturing a circuit device according to claim 1, wherein the insulating resin is molded by transfer molding or potting.

13. (Currently Amended) A method of manufacturing a circuit device comprising the steps of:

~~preparing a conductive foil and forming plural layers of a conductive pattern through an interlayer insulating film;~~

providing an interlayer insulating film over the conductive foil;

providing plural layers of a conductive pattern over the interlayer insulating film;

~~incorporating~~mounting a circuit element ~~into~~onto the conductive pattern ~~which is~~  
desirable;

covering the circuit element and molding a whole surface with an insulating resin; and  
removing the conductive foil.

14. (Original) A method of manufacturing a circuit device according to claim 13 further  
comprising the step of:

isolating the insulating resin through dicing for each circuit device including the circuit  
element.

15. (Original) The method of manufacturing a circuit device according to claim 13,  
wherein the conductive foil is constituted by any of copper, aluminum and iron-nickel.

16. (Original) The method of manufacturing a circuit device according to claim 13,  
wherein a thermosetting resin is used for the interlayer insulating film.

17. (Original) The method of manufacturing a circuit device according to claim 16,  
wherein a via hole is formed on the interlayer insulating film through a laser.

18. (Original) The method of manufacturing a circuit device according to claim 13,  
wherein a photosensitive resist layer is used for the interlayer insulating film.

19. (Original) The method of manufacturing a circuit device according to claim 18,  
wherein a via hole is formed on the interlayer insulating film through photosensitization.

20. (Original) The method of manufacturing a circuit device according to claim 13,  
wherein the conductive pattern of the layers is formed by a copper plated layer.

21. (Original) The method of manufacturing a circuit device according to claim 20,  
wherein the copper plated layer is formed by electroless plating and electroplating.

22. (Original) The method of manufacturing a circuit device according to claim 13, wherein the circuit element has either or both of a semiconductor bare chip and a chip circuit component fixed thereto.

23. (Original) The method of manufacturing a circuit device according to claim 13, wherein the insulating resin is molded by transfer molding or potting.

24. (New) The method of manufacturing a circuit device according to claim 1, wherein a thickness of said conductive foil is 70 to 300  $\mu\text{m}$ .

25. (New) The method of manufacturing a circuit device according to claim 13, wherein a thickness of said conductive foil is 70 to 300  $\mu\text{m}$ .

26. (New) The method of manufacturing a circuit device according to claim 1, wherein the circuit element is a face down semiconductor element.

27. (New) The method of manufacturing a circuit device according to claim 13, wherein the circuit element is a face down semiconductor element.